


2514096 CRIMSON SEMICONDUCTOR INC

99D 00335 D

T-33-01

EPITAXIAL BASE TO-3 (continued)


NPN	PNP	V _{ceo} (V)	V _{ceo} (V)	I _c (A)	P _{tot} (W)	h _{FE} min	I _c /V _{CE} (A/V)	V _{CE sat} max (V)	I _c /I _B (A/ma)	PACKAGE
2N3716	2N3792	100/80	80	10	150	30	3/2	0.8	5/500	
2N5873	2N5871	60	60	7	115	35	0.5/4	1	4/400	
2N5874	2N5872	80	80	7	115	35	0.5/4	1	4/400	
2N5877	2N5875	60	60	10	150	20	4/4	1	5/500	
2N5878	2N5876	80	80	10	150	20	4/4	1	5/500	
2N6055	2N6053	60	60	8	100	750	4/3	2	4/16	
2N6056	2N6054	80	80	8	100	750	4/3	2	4/16	
2N6057	2N6050	60	60	12	150	750	6/3	2	6/24	
2N6058	2N6051	80	80	12	150	750	6/3	2	6/24	
2N6059	2N6052	100	100	12	150	750	6/3	2	6/24	

* Darlington types TO-39


EPITAXIAL PLANAR

NPN and PNP types
 Good voltage capability (V_{CEs} up to 400 V)
 Low saturation voltage
 Low leakage
 Very high f_T (up to 100 MHz)
 Very high speed
 Moderate ruggedness
 Total base-collector passivation

EPITAXIAL PLANAR - TO-126

NPN	PNP	V _{ceo} (V)	V _{ceo} (V)	I _c (A)	P _{tot} (W)	h _{FE} min	I _c /V _{CE} (A/V)	V _{CE sat} max (V)	I _c /I _B (A/ma)	PACKAGE
BD135	BD136	45	45	1.5	12.5	40	0.15/2	0.5	0.5/50	
BD137	BD138	60	60	1.5	12.5	40	0.15/2	0.5	0.5/50	
BD139	BD140	80	80	1.5	12.5	40	0.15/2	0.5	0.5/50	
BD375	BD376	50	45	2	25	40	0.15/2	1	1/100	
BD377	BD378	75	60	2	25	40	0.15/2	1	1/100	
BD379	BD380	100	80	2	25	40	0.15/2	1	1/100	
BU325		200	200	3	25	30	0.5/5	1.5	0.5/50	

EPITAXIAL PLANAR - TO-220

NPN	V _{ceo} (V)	V _{ceo} (V)	I _c (A)	P _{tot} (W)	h _{FE} min	I _c /V _{CE} (A/V)	V _{CE sat} max (V)	I _c /I _B (A/ma)	PACKAGE
BU406	400	200	7	60	10	5/1	1	5/500	
BU406D	400	—	7	60	7.7	5/1	1	5/650	
BU406H	400	200	7	60	6.25	5/1	1	5/800	
BU407	330	150	7	60	10	5/1	1	5/500	
BU407D	330	—	7	60	7.7	5/1	1	5/650	
BU407H	330	150	7	60	6.25	5/1	1	5/800	
BU408	400	200	7	60	5	6/1	1	6/1200	
BU408D	400	—	7	60	5	6/1	1	6/1200	
BU409	250	150	7	60	7.5	3/1	1	3/400	
BU806	400	200	8	60	100	5/1.5	1.5	5/50	
BU807	330	150	8	60	100	5/1.5	1.5	5/50	

* Darlington types